

描述 / Descriptions

SOP-8 塑封封装 N 沟道 Power Trench MOS 双场效应管。

Dual N-Channel Power Trench MOSFET in a SOP-8 Plastic Package.

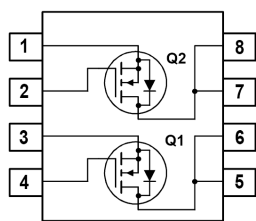
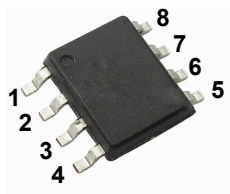
特征 / Features

- ◆ 低导通电阻，低门电荷，广泛应用于功率转换应用，无卤产品。
- ◆ Low RDS(ON), Low gate charge, use for a wide range of power conversion applications, HF Product.

用途 / Applications

电池保护，负载开关，电源管理。

Battery protection, Load Switch, Power management.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1:S2 PIN 2:G2 PIN 3 : S1 PIN 4 : G1

PIN5、PIN 6:D1 PIN 7、PIN 8 : D2

印章代码 / Marking

见印章说明。 See Marking Instructions.


极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	8	A
Pulsed Drain Current	I_{DM}	6	A
Power Dissipation($T_A=25^\circ\text{C}$)	P_D	2.0	W
Avalanche Current	I_{AS}	11.7	A
Avalanche energy(L=0.5mH)	E_{AS}	54.8	mJ
Maximum Junction-to-Ambient	$t \leq 10s$	62.5 90 40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient	Steady-State		
Maximum Junction-to Lead	Steady-State		
Operating and Junction Temperature Range	T_j T_{stg}	-55~150	$^\circ\text{C}$

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	40	45		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=4A$		19.9	22	m Ω
		$V_{GS}=4.5V$ $I_D=3A$		29.5	36	
Diode Forward Voltage	V_{SD}	$I_S=1A$ $V_{GS}=0V$		0.75	1.0	V


电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Input Capacitance	C_{iss}	$V_{DS}=10V$ $V_{GS}=0V$ $f=1.0MHz$		880		pF
Output Capacitance	C_{oss}			790		
Reverse Transfer Capacitance	C_{rss}			260		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_{GEN}=3\Omega$ $R_L=2.5\Omega$		4		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			15		
Turn-Off Fall Time	t_f			2		
Total Gate Charge	$Q_g(10V)$	$V_{GS}=10V$ $V_{DS}=20V$ $I_D=8A$		6.5		nC
Total Gate Charge	$Q_g(4.5V)$			3		
Gate-Source Charge	Q_{gs}			1.2		
Gate-Drain Charge	Q_{gd}			1,1		

电参数曲线图 / Electrical Characteristic Curve

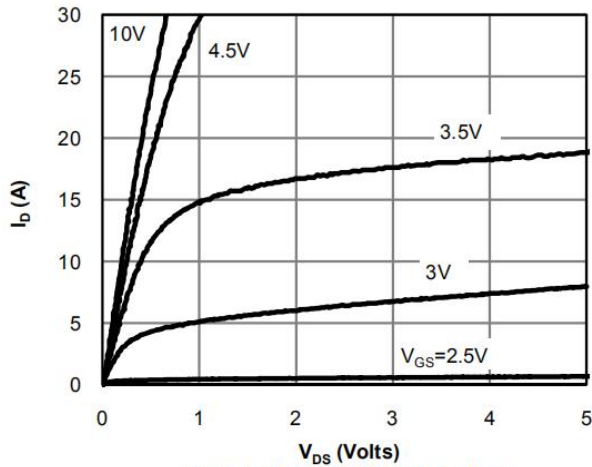


Fig 1: On-Region Characteristics

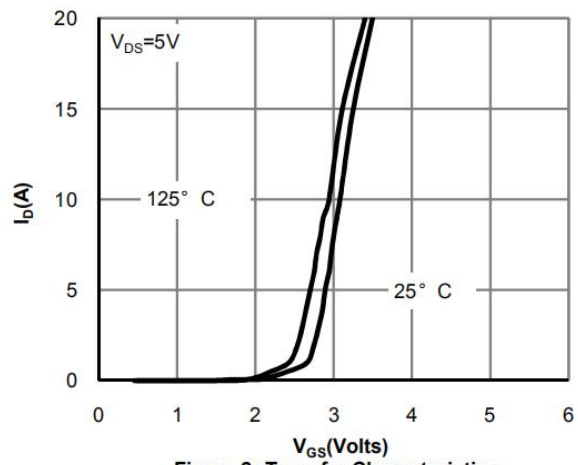


Figure 2: Transfer Characteristics

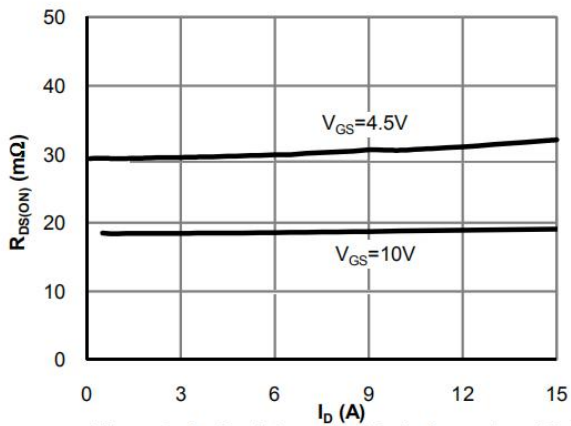


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

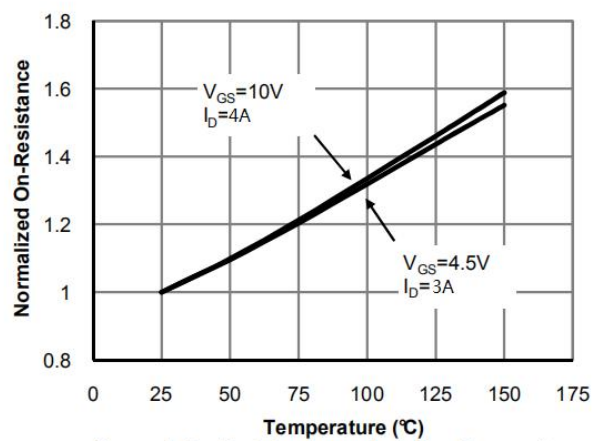


Figure 4: On-Resistance vs. Junction Temperature

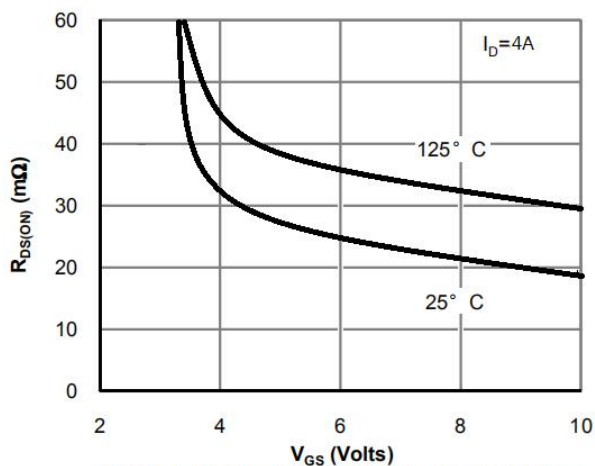


Figure 5: On-Resistance vs. Gate-Source Voltage

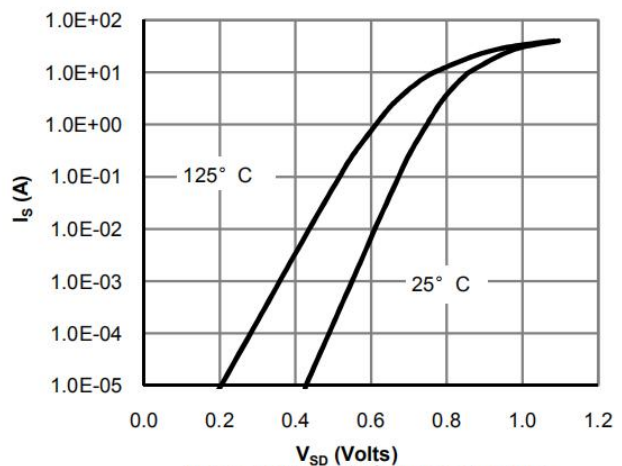
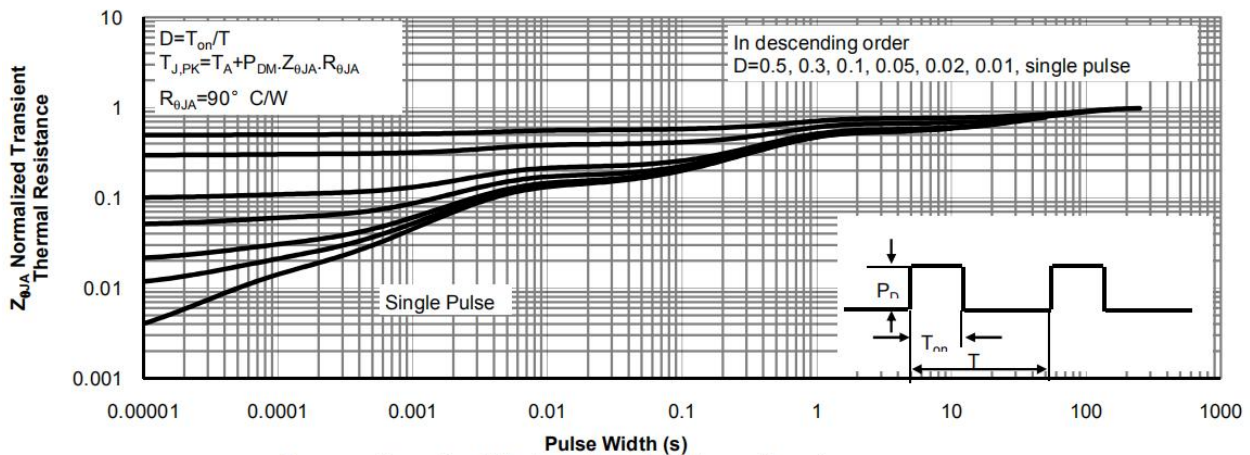
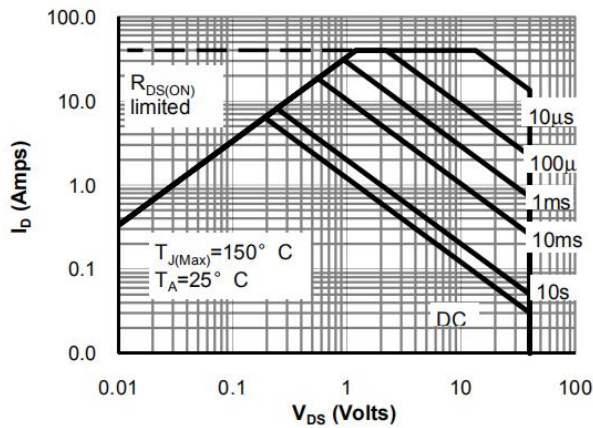
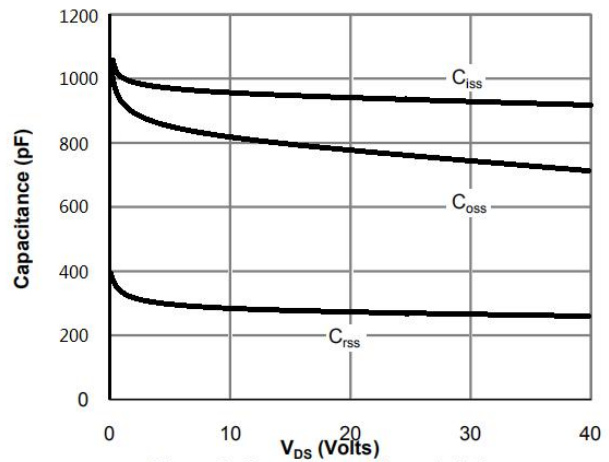
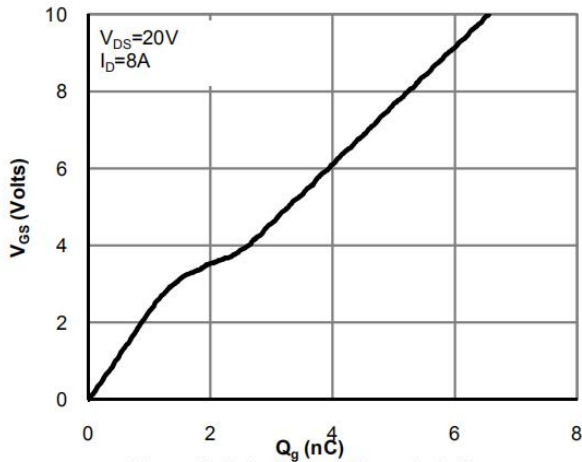


Figure 6: Body-Diode Characteristics

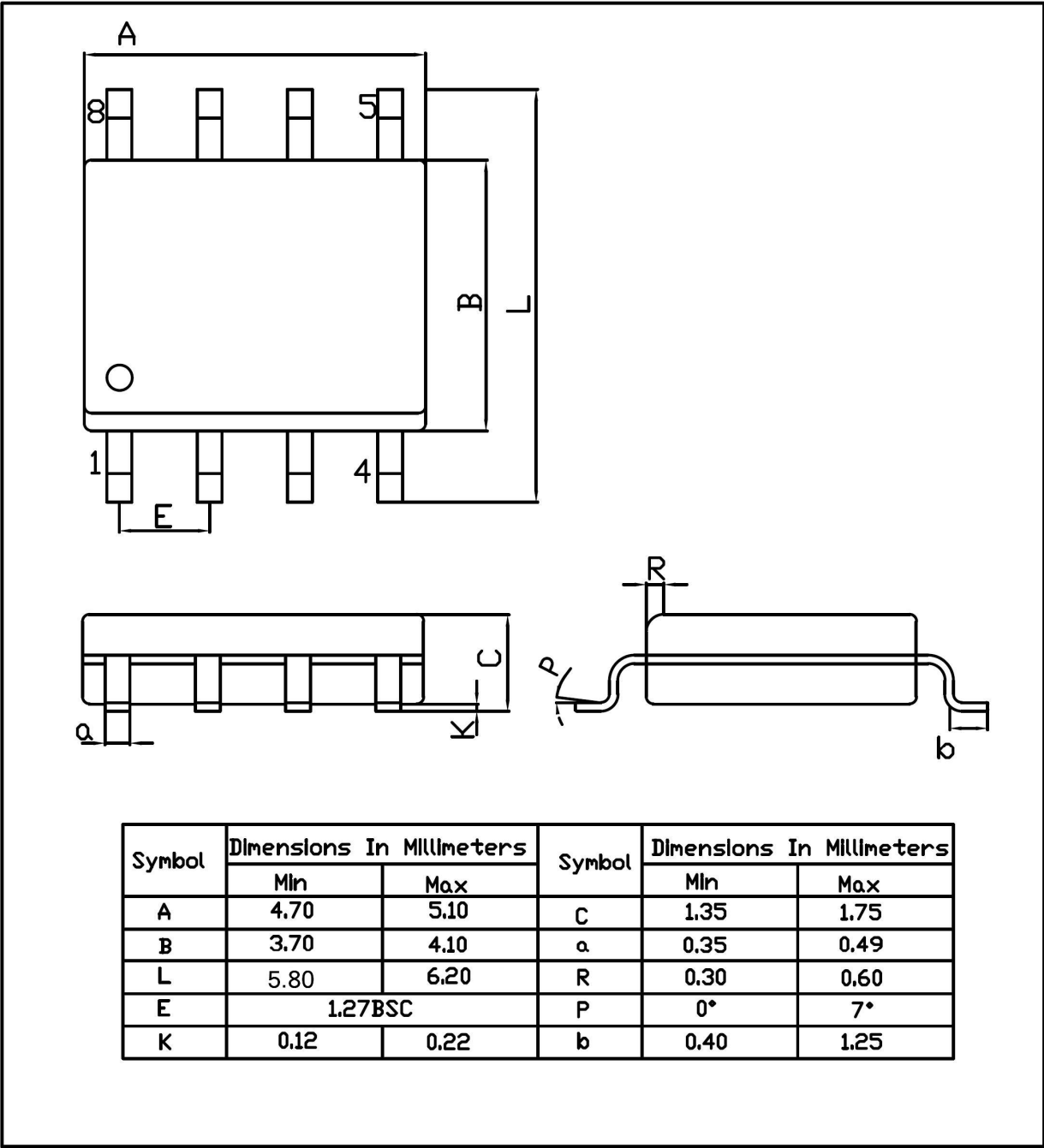
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

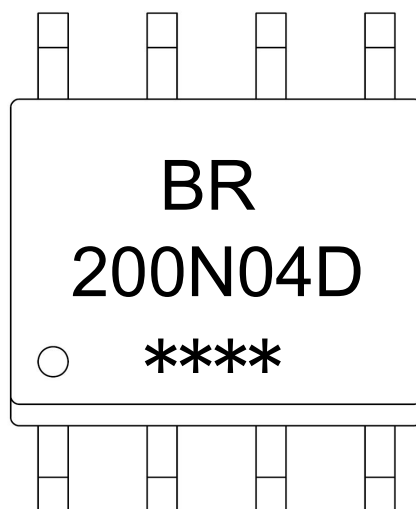
SOP-8

Unit:mm





印章说明 / Marking Instructions



说明：

BR： 为公司代码

200N04D： 为型号代码

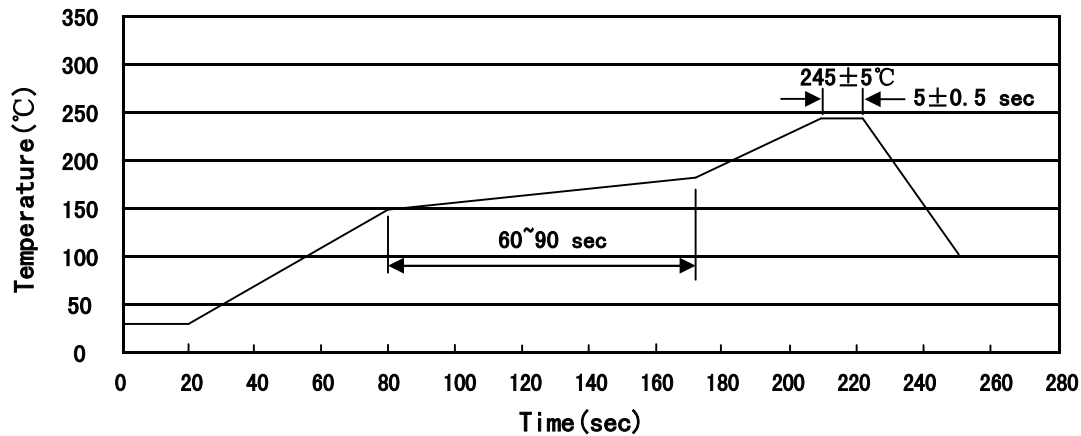
****： 为生产批号代码，随生产批号变化

Note:

BR: Company Code.

200N04D: Product Type.

****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices